

MBRD5200CT SCHOTTKY RECTIFIER

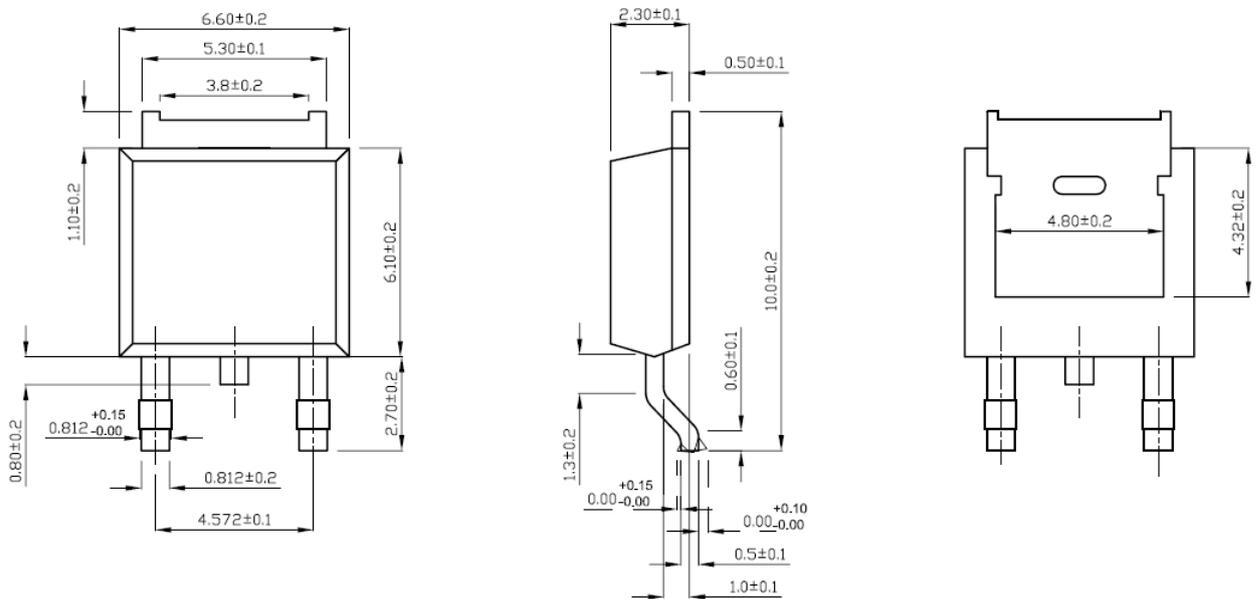
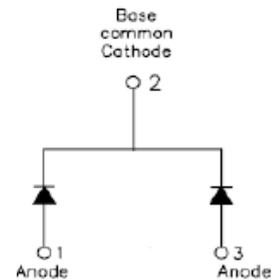
Applications:

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

Features:

- 150°C T_J operation
- Center tap configuration
- Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- This is a Pb - Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Mechanical Dimensions: In mm:



DPAK

Marking Diagram:


Where XXXXX is YYWWL

MBR	= Device Type
D	= Package type
5	= Forward Current (5A)
200	= Reverse Voltage (200V)
CT	= Configuration
SSG	= SSG
YY	= Year
WW	= Week
L	= Lot Number

Cautions: Molding resin
 Epoxy resin UL:94V-0

Ordering Information:

Device	Package	Shipping
MBRD5200CT	DPAK (Pb-Free)	2500pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V_{RWM}	-	200	V
Average Forward Current	$I_{F(AV)}$	50% duty cycle @ $T_C=105^\circ\text{C}$, rectangular wave form	5	A
Peak One Cycle Non-Repetitive Surge Current (per leg)	I_{FSM}	8.3 ms, half Sine pulse	60	A

Electrical Characteristics:

Characteristics	Symbol	Condition	Max.	Units
Forward Voltage Drop(per leg)*	V_{F1}	@ 2.5 A, Pulse, $T_C = 25\text{ }^\circ\text{C}$ @ 5 A, Pulse, $T_C = 25\text{ }^\circ\text{C}$	0.85 0.95	V
	V_{F2}	@ 2.5 A, Pulse, $T_C = 125\text{ }^\circ\text{C}$ @ 5 A, Pulse, $T_C = 125\text{ }^\circ\text{C}$	0.75 0.85	V
Reverse Current at DC Condition(per leg)	I_{R1}	@ $V_R = \text{rated } V_R$ $T_J = 25\text{ }^\circ\text{C}$	1.0	mA
	I_{R2}	@ $V_R = \text{rated } V_R$ $T_J = 125\text{ }^\circ\text{C}$	7.0	mA
Junction Capacitance(per leg)	C_T	@ $V_R = 5\text{V}$, $T_C = 25\text{ }^\circ\text{C}$ $f_{SIG} = 1\text{MHz}$	150	pF
Voltage Rate of Change	dv/dt	-	10,000	V/ μs

* Pulse Width < 300 μs , Duty Cycle <2%

Thermal-Mechanical Specifications:

Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	T_J	-	-55 to +150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-	-55 to +150	$^\circ\text{C}$
Maximum Thermal Resistance Junction to Case	$R_{\theta JC}$	DC operation	6	$^\circ\text{C/W}$
Approximate Weight	wt	-	0.39	g
Case Style	DPAK			

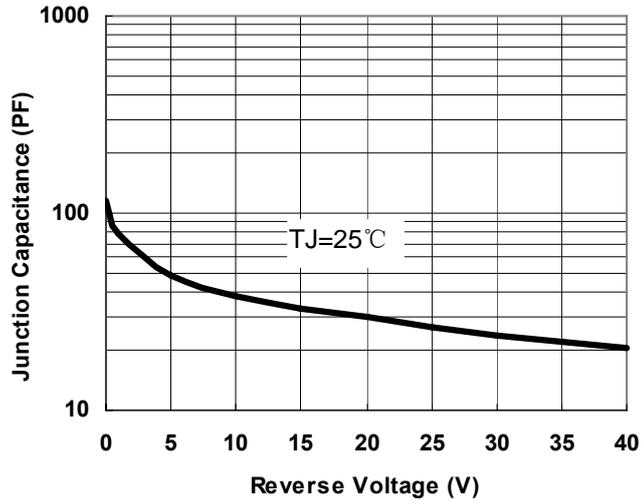


Fig.1-Typical Junction Capacitance

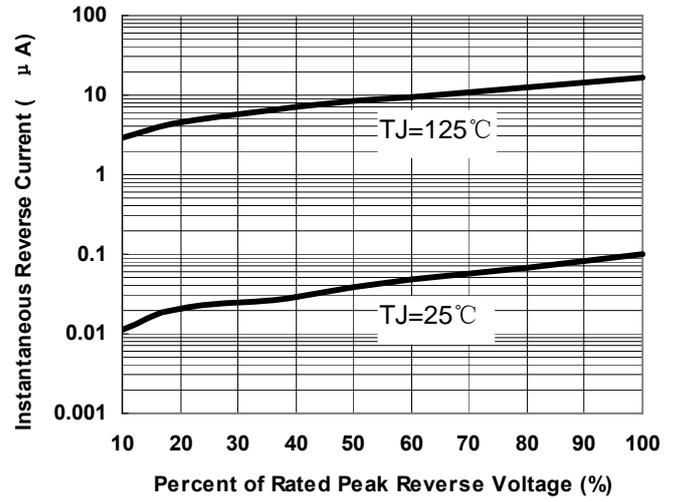


Fig.2-Typical Reverse Characteristics

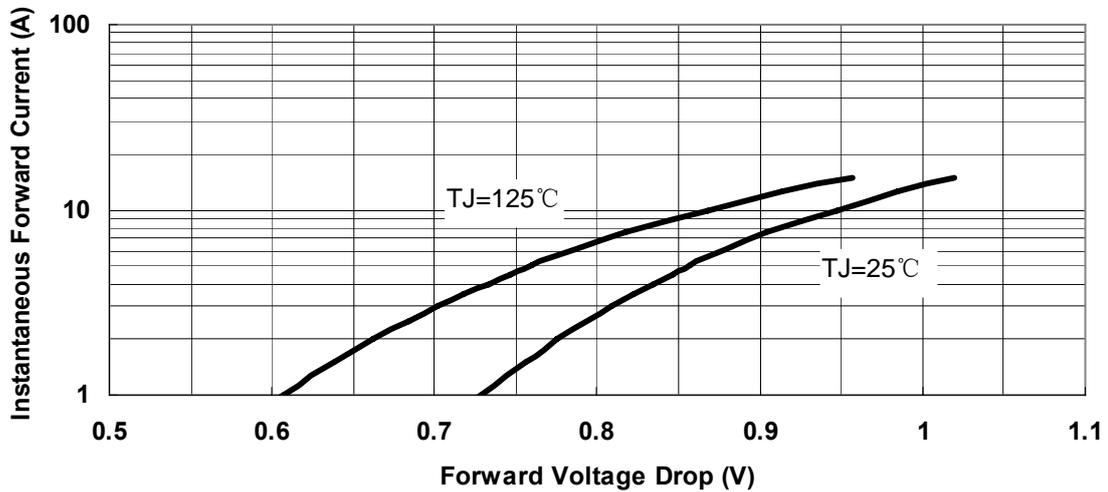


Fig.3-Typical Instantaneous Forward Voltage Characteristics

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